



FORM PTO-1449 (SUBSTITUTE)

Attorney Docket No.:

Applic. No.

P2001,0216

10/673,705

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))

Applicant

Annalisa Cappellani et al.

Filing Date

Group Art Unit

September 26, 2003

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
SBG	A	6,277,699 B1	08/21/01	Chen et al.	—	—	
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	381309	09/19/98	Taiwan			X
	K						
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	
	P	

EXAMINER

DATE CONSIDERED

6/7/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with
next communication to applicant.

Sheet 1 of 3

FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: P2001,0216 Appl. No.: Applicant: ANNALISA CAPPELLANI ET AL. Filing Date: September 26, 2003 Group Art Unit:			
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
SBG	A	6,091,120	7/18/00	Yeom et al.	—	—	
SBG	B	5,089,863	2/18/92	Sato et al.	—	—	
SBG	C	5,384,479	1/24/95	Taniguchi	—	—	
	D						
	E						
	F						
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
SBG	J	42 34 528 C2	4/15/93	Germany	—	—	X
SBG	K	42 34 777 A1	4/21/94	Germany	—	—	X
SBG	L	2 791 177 A1	9/22/00	France	—	—	
	M	09044768	2/25/88	Japan			
SBG	N	0 740 334 A2	10/30/96	Europe	—	—	X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
SBG		Widmann, D. et al.: "Technologie hochintegrierter Schaltungen" [Technology of High-Density Integrated Circuits], Springer Verlag, 2 nd Edition, pp. 201-203					
SBG		Ghani, T. et al.: "100nm Gate Length High Performance/Low Power CMOS Transistor Structure", IEEE, 1999, pp. 415-418					
EXAMINER <i>John B. Bz</i>				DATE CONSIDERED <i>6/7/04</i>			

BEST AVAILABLE COPY

FORM PTO-1449 (SUBSTITUTE)				Attorney Docket No.: P2001,0216																																																																											
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				Appl. No.:																																																																											
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Applicant: ANNALISA CAPPELLANI ET AL.																																																																											
				Filing Date: September 26, 2003																																																																											
				Group Art Unit:																																																																											
<table border="1"><thead><tr><th>EXAMINER INITIALS</th><th></th><th>PATENT NO.</th><th>DATE</th><th>PATENTEE</th><th>CLASS</th><th>SUB CLASS</th><th>FILING DATE</th></tr></thead><tbody><tr><td rowspan="9"></td><td>A</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>B</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>C</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>D</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>E</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>F</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>G</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>H</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>I</td><td></td><td></td><td></td><td></td><td></td><td></td></tr></tbody></table>								EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE		A							B							C							D							E							F							G							H							I						
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE																																																																								
	A																																																																														
	B																																																																														
	C																																																																														
	D																																																																														
	E																																																																														
	F																																																																														
	G																																																																														
	H																																																																														
	I																																																																														
FOREIGN PATENT DOCUMENT																																																																															
<table border="1"><thead><tr><th></th><th></th><th>DOCUMENT NO.</th><th>DATE</th><th>COUNTRY</th><th>CLASS</th><th>SUB CLASS</th><th>TRANSL. YES NO</th></tr></thead><tbody><tr><td>SBG</td><td>J</td><td>0 328 350 A2</td><td>8/18/89</td><td>Europe</td><td>—</td><td>—</td><td>X </td></tr><tr><td>SBG</td><td>K</td><td>02/41383 A1</td><td>5/23/02</td><td>WIPO</td><td>—</td><td>—</td><td>X </td></tr><tr><td rowspan="3"></td><td>L</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>M</td><td></td><td></td><td></td><td></td><td></td><td></td></tr><tr><td>N</td><td></td><td></td><td></td><td></td><td></td><td></td></tr></tbody></table>										DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO	SBG	J	0 328 350 A2	8/18/89	Europe	—	—	X	SBG	K	02/41383 A1	5/23/02	WIPO	—	—	X		L							M							N																																
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO																																																																								
SBG	J	0 328 350 A2	8/18/89	Europe	—	—	X																																																																								
SBG	K	02/41383 A1	5/23/02	WIPO	—	—	X																																																																								
	L																																																																														
	M																																																																														
	N																																																																														
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)																																																																															
SBG		Lasky, J. B. et al.: "Comparison of Transformation to Low-Resistivity Phase and Agglomeration of TiSi_2 and CoSi_2 ", IEEE Transactions on Electron Devices, Vol. 38, No. 2, February 1991, pp. 262-269																																																																													
SBG		Hisamoto, D. et al.: "A Low-Resistance Self-Aligned T-Shaped Gate for High-Performance Sub-0.1- μm CMOS", IEEE Transactions on Electron Devices, Vol. 44, No. 6, June 1997, pp. 951-956																																																																													
EXAMINER		DATE CONSIDERED			6/7/04																																																																										

BEST AVAILABLE COPY

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: P2001,0216					
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Appl. No.:					
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Applicant: ANNALISA CAPPELLANI ET AL.					
		Filing Date: September 26, 2003					
		Group Art Unit:					
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
	K						
	L						
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
586		Kasai, K. et al.: "W/WNx/Poly-Si Gate Technology for Future High Speed Deep Submicron CMOS LSIs", IEEE, 1994, pp. 497-500					
EXAMINER				DATE CONSIDERED 6/7/04			

BEST AVAILABLE COPY